32-bit bus transceiver with direction pin; 5 V tolerant; 3-stateRev. 01 — 20 August 2007Product data sheet

Product data sheet

1. **General description**

The 74LVC32245A is a 32-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The device features four output enable (nOE) inputs for easy cascading and four send/receive (nDIR) inputs for direction control. Pin $n\overline{OE}$ controls the outputs so that the buses are effectively isolated.

Inputs can be driven from either 3.3 V or 5 V devices. When disabled, up to 5.5 V can be applied to the outputs. These features allow the use of these devices in mixed 3.3 V and 5 V applications.

To ensure the high-impedance state during power-up or power-down, pin nOE should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

2. **Features**

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low power consumption
- MULTIBYTE flow-through standard pin-out architecture
- Low inductance multiple power and ground pins for minimum noise and ground bounce
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- High-impedance when V_{CC} = 0 V
- Complies with JEDEC standard JESD8-B / JESD36
- ESD protection:
 - HBM EIA/JESD22-A114-B exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
- Specified from –40 °C to +85 °C
- Packaged in plastic fine-pitch ball grid array package

Ordering information 3.

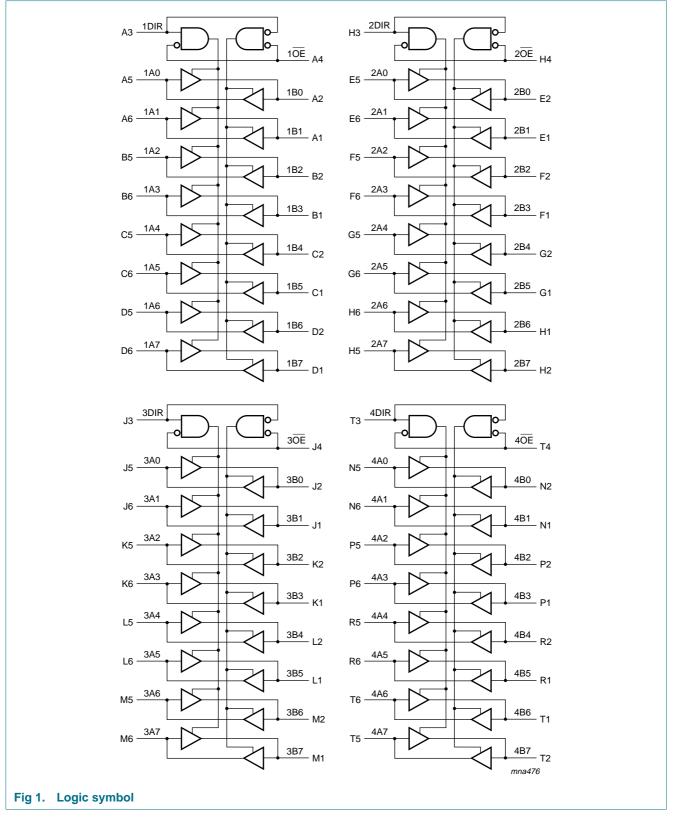
Table 1. **Ordering information**

Type number	Package			
	Temperature range	Name	Description	Version
74LVC32245AEC	–40 °C to +85 °C	LFBGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body $13.5 \times 5.5 \times 1.05$ mm	SOT536-1



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4. Functional diagram



⁷⁴LVC32245A_1 Product data sheet

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5. Pinning information

5.1 Pinning

										-								r	nna475
			6	1A1	1A3	1A5	1A7	2A1	2A3	2A5	2A6	3A1	3A3	3A5	3A7	4A1	4A3	4A5	4A6
			5	1A0	1A2	1A4	1A6	2A0	2A2	2A4	2A7	3A0	3A2	3A4	3A6	4A0	4A2	4A4	4A7
			4	10E	GND	VCC	GND	GND	Vcc	GND	20E	30E	GND	Vcc	GND	GND	Vcc	GND	40E
			3	1DIR	GND	Vcc	GND	GND	Vcc	GND	2DIR	3DIR	GND	V _{CC}	GND	GND	V _{CC}	GND	4DIR
			2	1B0	1B2	1B4	1B6	2B0	2B2	2B4	2B7	3B0	3B2	3B4	3B6	4B0	4B2	4B4	4B7
			1	1B1	1B3	1B5	1B7	2B1	2B3	2B5	2B6	3B1	3B3	3B5	3B7	4B1	4B3	4B5	4B6
				A	В	С	D	Е	F	G	н	J	к	L	М	N	Р	R	т
Fig 2.	Pin	config	gura	ation															

5.2 Pin description

Table 2. Pin description

Pin name	Ball	Description
nDIR (n = 1 to 4)	A3, H3, J3, T3	direction control
$n\overline{OE}$ (n = 1 to 4)	A4, H4, J4, T4	output enable input (active LOW)
1A[0:7]	A5, A6, B5, B6, C5, C6, D5, D6	input or output
1B[0:7]	A2, A1, B2, B1, C2, C1, D2, D1	input or output
2A[0:7]	E5, E6, F5, F6, G5, G6, H6, H5	input or output
2B[0:7]	E2, E1, F2, F1, G2, G1, H1, H2	input or output
3A[0:7]	J5, J6, K5, K6, L5, L6, M5, M6	input or output
3B[0:7]	J2, J1, K2, K1, L2, L1, M2, M1	input or output
4A[0:7]	N5, N6, P5, P6, R5, R6, T6, T5	input or output
4B[0:7]	N2, N1, P2, P1, R2, R1, T1, T2	input or output
GND	B3, B4, D3, D4, E3, E4, G3, G4, K3, K4, M3, M4, N3, N4, R3, R4	ground (0 V)
V _{CC}	C3, C4, F3, F4, L3, L4, P3, P4	supply voltage

6. Functional description

Table 3. Function selection ^[1]						
Input		Output				
nOE	nDIR	nAn	nBn			
L	L	A = B	inputs			
L	Н	inputs	B = A			
Н	Х	Z	Z			

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{O} > V_{CC}$ or $V_{O} < 0 V$	-	±50	mA
Vo	output voltage	output HIGH or LOW state	[2] -0.5	$V_{CC} + 0.5$	V
		output 3-state	[2] -0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		<u>[3]</u>	200	mA
I _{GND}	ground current		<u>[3]</u> –200	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +85 \ ^{\circ}C$	[4] _	1000	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] All supply and ground pins connected externally to one voltage source.

[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage	for maximum speed performance	2.7	-	3.6	V
		for low-voltage applications	1.2	-	-	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	output HIGH or LOW state	0	-	V _{CC}	V
		output 3-state	0	-	5.5	V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.2 V to 2.7 V	-	-	20	ns/V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	10	ns/V

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9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	V _{CC} (V)	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -4	40 °C to +85 °C						
V _{IH}	HIGH-level input voltage		1.2	V _{CC}	-	-	V
			2.7 to 3.6	2.0	-	-	V
V _{IL}	LOW-level input voltage		1.2	-	-	GND	V
			2.7 to 3.6	-	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$					
	I _O = −100 μA	2.7 to 3.6	$V_{CC}-0.2$	V _{CC}	-	V	
		$I_{O} = -12 \text{ mA}$	2.7	$V_{CC}-0.5$	-	-	V
	I _O = -18 mA	3.0	$V_{CC} - 0.6$	-	-	V	
		I _O = -24 mA	3.0	$V_{CC}-0.8$	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$					
		I _O = 100 μA	2.7 to 3.6	-	GND	0.20	V
		I _O = 12 mA	2.7	-	-	0.40	V
		I _O = 24 mA	3.0	-	-	0.55	V
I	input leakage current	$V_I = 5.5 V \text{ or GND}$	3.6	-	±0.1	±5	μA
I _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = 5.5 \text{ V or GND}$	3.6	[2] -	±0.1	±5	μA
I _{OFF}	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}$	0.0	-	±0.1	±10	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A	3.6	-	0.1	40	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}$	2.7 to 3.6	-	5	500	μA
CI	input capacitance	$V_I = GND$ to V_{CC}	0 to 3.6	-	5.0	-	pF
C _{I/O}	input/output capacitance	$V_I = GND$ to V_{CC}	0 to 3.6	-	10	-	pF

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

[2] For I/O ports the parameter I_{OZ} includes the input leakage current.

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10. Dynamic characteristics

Table 7. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 5.

Symbol	Parameter	Conditions	V _{CC} (V)		Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -	40 °C to +85 °C							
t _{pd}	propagation delay	nAn to nBn; nBn to nAn;	1.2	[2]	-	13.0	-	ns
		see Figure 3	2.7		1.0	2.7	4.7	ns
			3.0 to 3.6		1.0	2.2	4.5	ns
t _{en}	enable time	nOE to nAn, nBn: see Figure 4	1.2	[2]	-	15.0	-	ns
		2.7		1.5	3.6	6.7	ns	
			3.0 to 3.6		1.0	2.8	5.5	ns
t _{dis}	disable time	n OE to nAn, nBn; see <u>Figure 4</u>	1.2	[2]	-	11.0	-	ns
			2.7		1.5	3.4	6.6	ns
			3.0 to 3.6		1.5	3.2	5.6	ns
t _{sk(o)}	output skew time		3.0 to 3.6	[3]	-	-	1.0	ns
C _{PD}	power dissipation capacitance	per buffer; $V_I = GND$ to V_{CC}	3.3	<u>[4]</u>	-	30	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 2.7 V, and 3.3 V respectively.

- [2] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- [3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz; f_o = output frequency in MHz

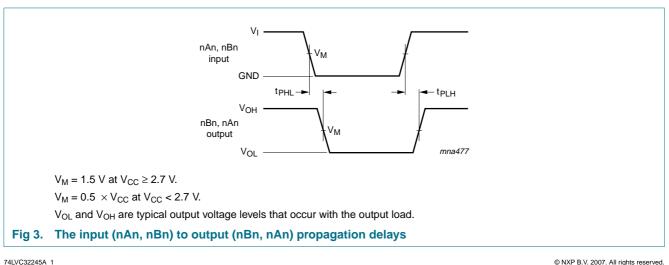
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

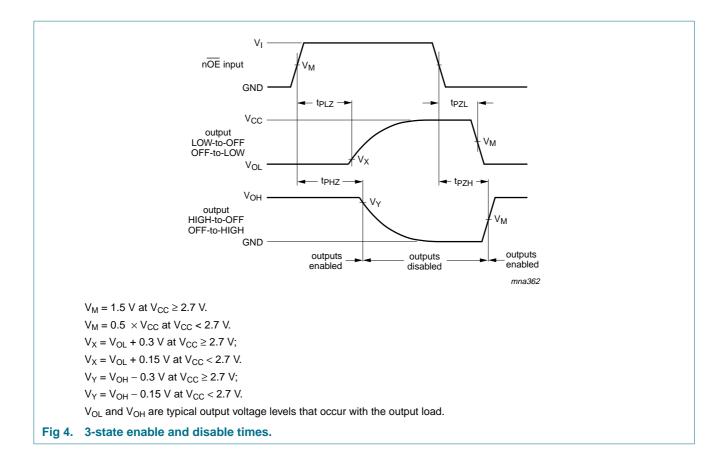
11. Waveforms



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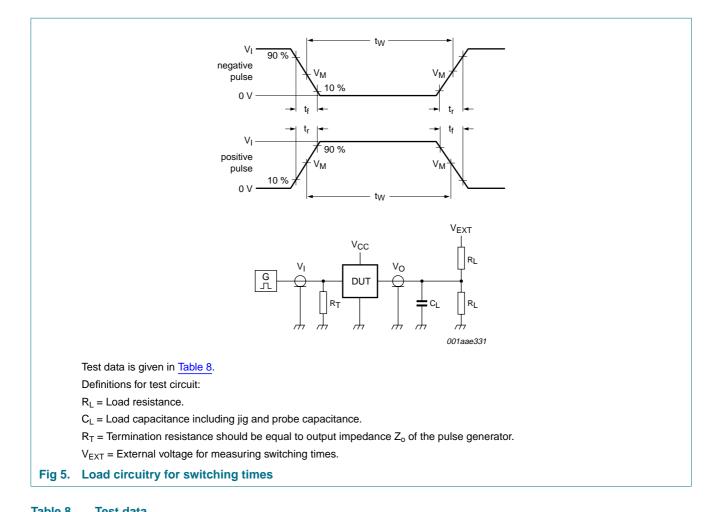
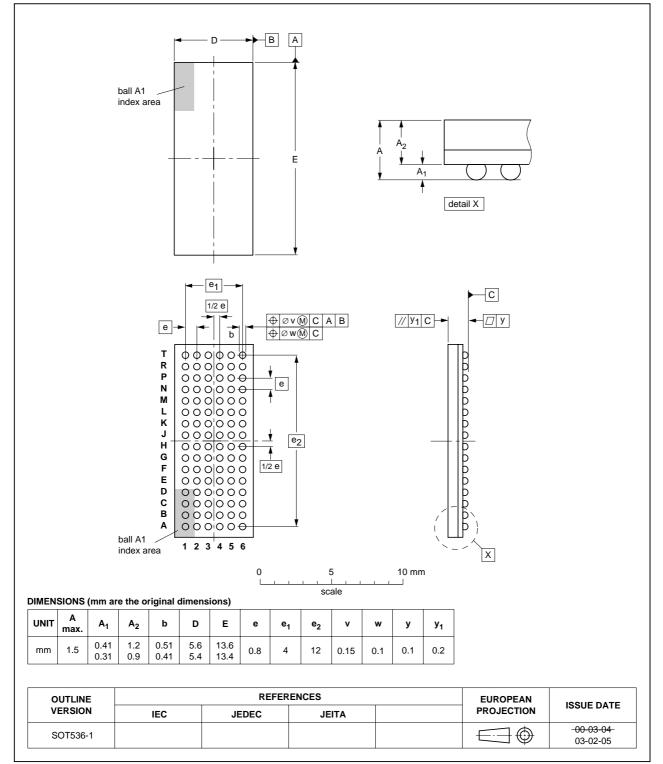


Table 8. Test data							
Supply voltage	Input		Load		V _{EXT}		
	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.2 V	V _{CC}	\leq 2 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND

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12. Package outline



LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1

Fig 6. Package outline SOT536-1 (LFBGA96)

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13. Abbreviations

Table 9.	Abbreviations
Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 10. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC32245A_1	20070820	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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